

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	30109	tensile adj stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 12:59
L2	18616	compressive adj stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 12:59
L3	6091	1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:35
L4	121244	CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:36
L5	435	3 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:36
L6	416485	(silicon adj nitride) or SiN or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:36
L7	247499	(silicon adj (oxynitride or oxy-nitride)) or SiON or SiNO or Si-O-N	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:36
L8	42246	6 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:37

L9	88	8 and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:37
L10	98875	NMOS or N-MOS or (N adj MOS) or NFET or N-FET or (N adj FET) or (N adj3 transistor\$1) or NMOSFET or N-MOSFET or (N adj MOSFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:02
L11	87180	PMOS or P-MOS or (P adj MOS) or PFET or P-FET or (P adj FET) or (P adj3 transistor\$1) or PMOSFET or P-MOSFET or (P adj MOSFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:03
L12	82	1 with 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:40
L13	90	2 with 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:41
L14	65	12 and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:41
L15	9	14 and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:41
L16	2	(("6069049") or ("6399976")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/12 11:30
L17	5	(("20040113217") or ("20040104405") or ("20040075148") or ("20030040158") or ("6573172")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/12 11:34
L18	1	("6825529").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/12 11:34

L19	14	("20020027254"   "20020076947"   "20020197861"   "5677232"   "6057581"   "6075262"   "6157064"   "6194748"   "6258695"   "6277683"   "6316302"   "6391782"   "6512273"   "6524901").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/12 12:31
L20	0	("6825529").URPN.	USPAT	OR	OFF	2005/05/12 12:53
L21	41706	silicid\$8	US-PGPUB; USPAT	OR	OFF	2005/05/12 12:53
L22	1	("20040104405").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/12 12:53
L23	0	21 and 22	US-PGPUB; USPAT	OR	OFF	2005/05/12 12:53
L24	42454	silicid\$8 or salicid\$8	US-PGPUB; USPAT	OR	OFF	2005/05/12 13:08
L25	0	22 and 24	US-PGPUB; USPAT	OR	OFF	2005/05/12 12:54
L26	338171	tensile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 12:58
L27	2035642	compress\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 12:59
L28	1260007	stress\$4 or strain\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:01
L29	55778	26 near5 28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:01
L30	62111	27 near5 28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:02

L31	17593	29 and 30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:02
L32	115147	NMOS or N-MOS or (N adj3 MOS) or NFET or N-FET or (N adj3 FET) or (N adj3 transistor\$1) or NMOSFET or N-MOSFET or (N adj3 MOSFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:03
L33	100457	PMOS or P-MOS or (P adj3 MOS) or PFET or P-FET or (P adj3 FET) or (P adj3 transistor\$1) or PMOSFET or P-MOSFET or (P adj3 MOSFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:04
L34	204370	4 or 32 or 33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:05
L35	860	34 and 31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:28
L36	591	35 and (6 or 7)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:07
L37	235	36 and 24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:07
L38	14886	(titanium or cobalt) near3 (silicid\$8 or salicid\$8)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:09

L39	69877	silicid\$8 or salicid\$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:09
L40	235	36 and 39	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:10
L41	93	40 and 38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:10
L42	767	35 not 41	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 13:28
S1	30084	tensile adj stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:35
S2	18601	compressive adj stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:35
S3	6084	S1 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/11 19:31
S4	121086	CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:36

S5	431	S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/11 19:35
S6	416154	(silicon adj nitride) or SiN or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:36
S7	247456	(silicon adj (oxynitride or oxy-nitride)) or SiON or SiNO or Si-O-N	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 10:36
S8	42207	S6 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/11 19:37
S9	87	S8 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/11 19:37